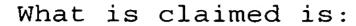
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- 1. An electroplating solution comprising copper ions and a complexing agent for the copper ions and having a pH in the range of 4 to 10.
- 2. An electroplating process using an electroplating solution comprising copper ions and a complexing agent for the copper ions and having a pH in the range of 4 to 10.
- 3. The electroplating process according to claim 2, wherein the plating is applied on the silicon wafer on which a conductive seed layer has been formed.
- 4. A silicon wafer plated with an electroplating solution comprising copper ions and a complexing agent for the copper ions and having a pH in the range of 4 to 10.